

150V NPN MEDIUM POWER TRANSISTOR IN SOT223

Features

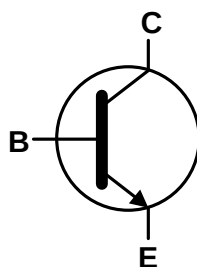
- $BV_{CEO} > 150V$
- $I_C = 5A$ High Continuous Collector Current
- $I_{CM} = 10A$ Peak Pulse Current
- Very Low Saturation Voltage $V_{CE(sat)} < 110mV$ @ 1A
- $R_{CE(sat)} = 50m\Omega$ for a Low Equivalent On-Resistance
- h_{FE} Specified Up to 10A for a High Gain Hold-Up
- Complementary PNP Type: FZT955
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

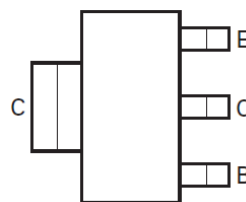
- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound; UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Plated Leads; Solderable per MIL-STD-202, Method 208 (B3)
- Weight: 0.112 grams (Approximate)



Top View



Device Symbol

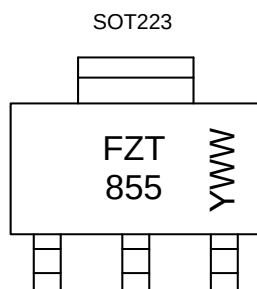
Top View
Pin-Out

Ordering Information (Note 4)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
FZT855TA	FZT855	7	12	1,000

- Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



FZT 855 = Product Type Marking Code
 YWW = Date Code Marking
 Y or $\bar{Y}$ = Last Digit of Year (ex: 5= 2015)
 WW or $\bar{W}W$ = Week Code (01~53)

Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	250	V
Collector-Emitter Voltage	V _{CEO}	150	V
Emitter-Base Voltage	V _{EBO}	7	V
Continuous Collector Current	I _C	5	A
Peak Pulse Current	I _{CM}	10	A
Base Current	I _B	1	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

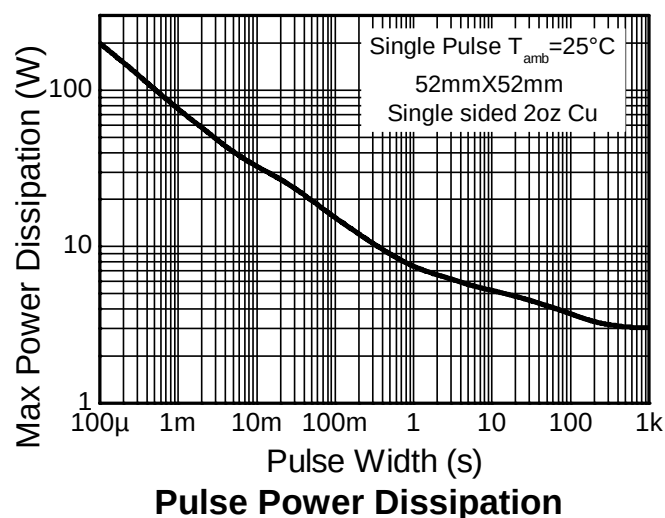
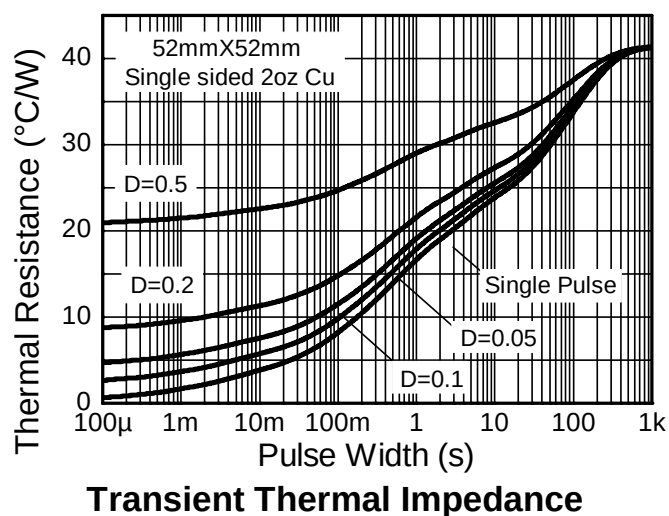
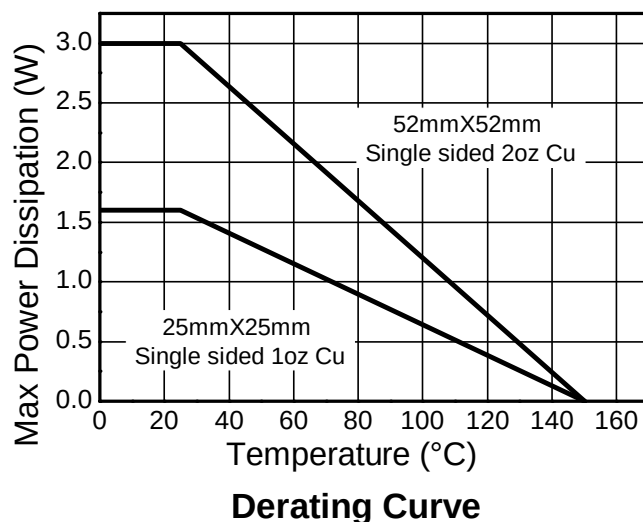
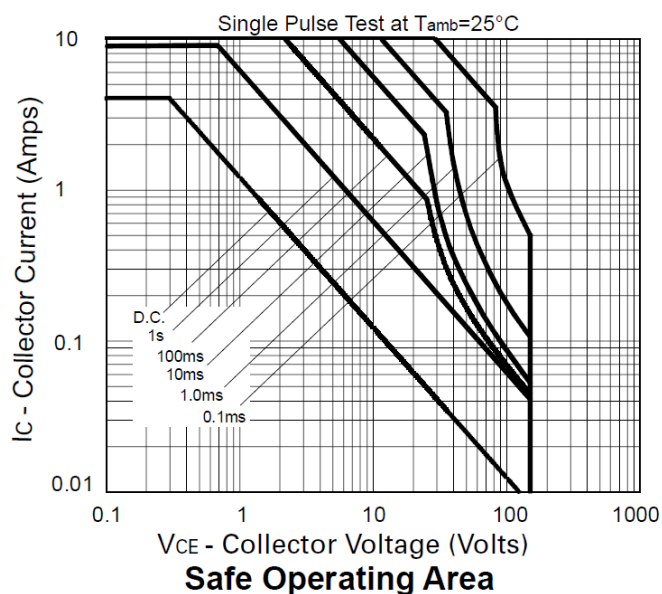
Characteristic		Symbol	Value	Unit
Power Dissipation	(Note 5)	P _D	3.0	W
Linear Derating Factor	(Note 6)		24	
			1.6	mW/°C
			12.8	
Thermal Resistance, Junction to Ambient	(Note 5)	R _{θJA}	42	°C/W
	(Note 6)	R _{θJA}	78	
Thermal Resistance Junction to Lead	(Note 7)	R _{θJL}	8.8	°C
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	

ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	≥ 8,000	V	3B
Electrostatic Discharge - Machine Model	ESD MM	≥ 400	V	C

- Notes:
5. For a device surface mounted on 52mm X 52mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions; device measured when operating in steady state condition.
 6. Same as Note 5, except the device is mounted on 25mm X 25mm single sided 1oz weight copper.
 7. Thermal resistance from junction to solder-point (at the end of the collector lead).
 8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

Thermal Characteristics and Derating Information

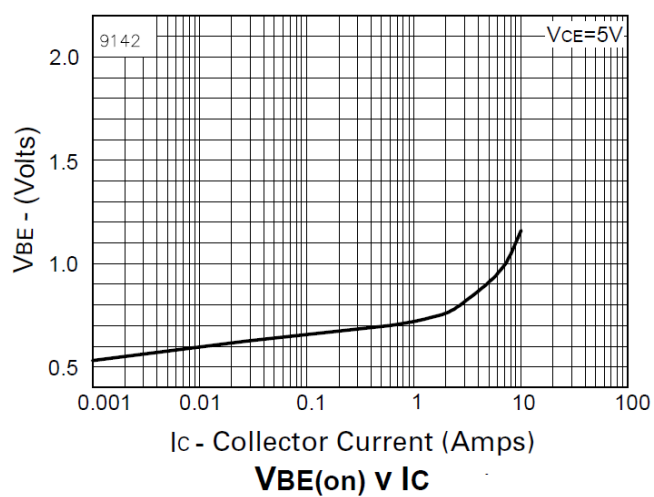
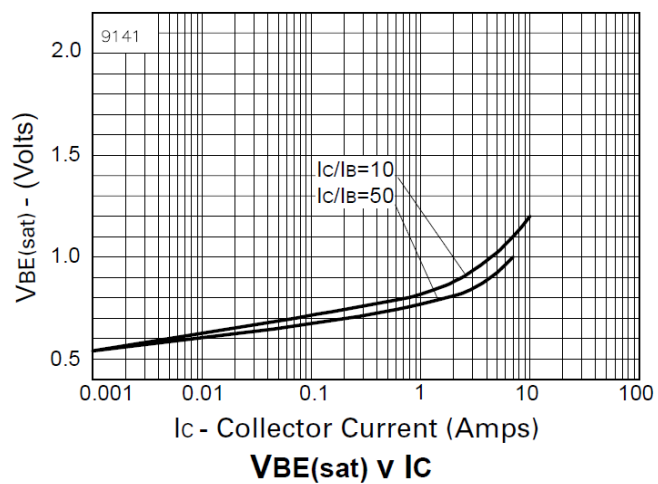
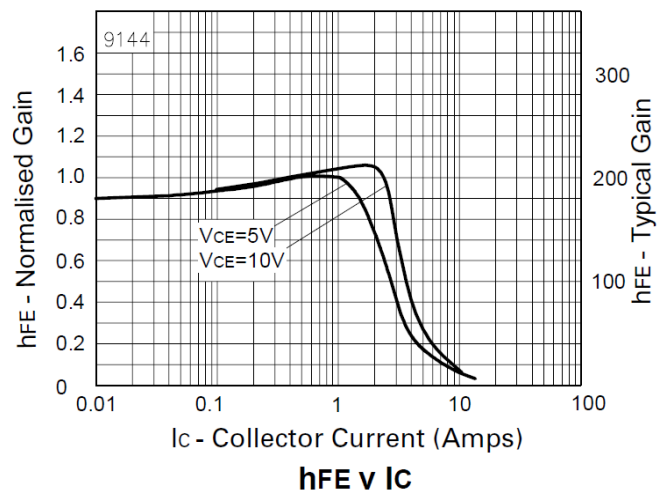
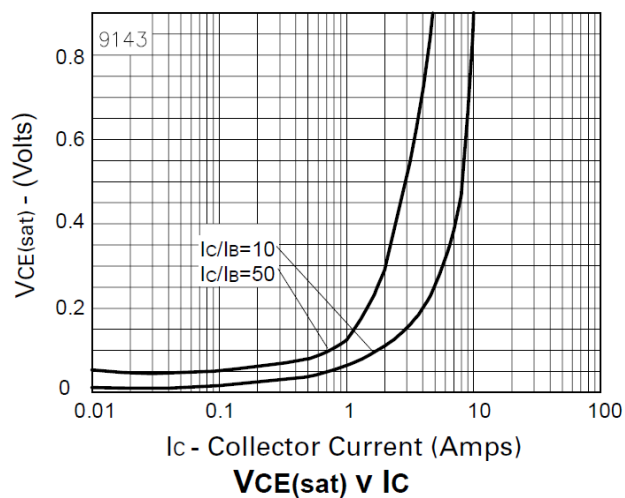


Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

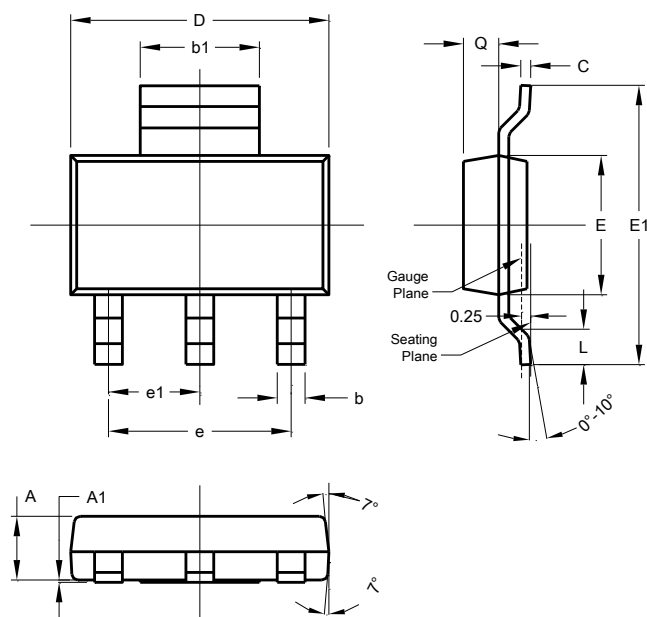
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	250	375	–	V	I _C = 100μA
Collector-Emitter Breakdown Voltage	BV _{CER}	250	375	–	V	I _C = 1μA, R _B ≤ 1kΩ
Collector-Emitter Breakdown Voltage (Note 9)	BV _{CEO}	150	180	–	V	I _C = 1mA
Emitter-Base Breakdown Voltage	BV _{EBO}	7	8	–	V	I _E = 100μA
Collector Cut-Off Current	I _{CBO}	–	–	50 1	nA μA	V _{CB} = 200V V _{CB} = 200V, @T _A = +100°C
Collector Cut-Off Current	I _{CER} R ≤ 1kΩ	–	–	50 1	nA μA	V _{CB} = 200V V _{CB} = 200V, @T _A = +100°C
Emitter Cut-Off Current	I _{EBO}	–	–	10	nA	V _{EB} = 6V
Collector-Emitter Saturation Voltage (Note 9)	V _{CE(sat)}	–	20 35 60 260	40 65 110 355	mV	I _C = 100mA, I _B = 5mA I _C = 500mA, I _B = 50mA I _C = 1A, I _B = 100mA I _C = 5A, I _B = 500mA
Base-Emitter Saturation Voltage (Note 9)	V _{BE(sat)}	–	–	1250	mV	I _C = 5A, I _B = 500mA
Base-Emitter Turn-On Voltage (Note 9)	V _{BE(on)}	–	–	1100	mV	I _C = 5A, V _{CE} = 5V
DC Current Gain (Note 9)	h _{FE}	100 100 15	200 200 30 10	– 300 – –		I _C = 10mA, V _{CE} = 5V I _C = 1A, V _{CE} = 5V I _C = 5A, V _{CE} = 5V I _C = 10A, V _{CE} = 5V
Current Gain-Bandwidth Product (Note 9)	f _T	–	90	–	MHz	V _{CE} = 10V, I _C = 100mA f = 50MHz
Output Capacitance (Note 9)	C _{obo}	–	22	–	pF	V _{CB} = 10V, f = 1MHz
Switching Times	t _{on} t _{off}	–	66 2130	–	ns ns	I _C = 1A, V _{CC} = 50V I _{B1} = -I _{B2} = 100mA

Note: 9. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

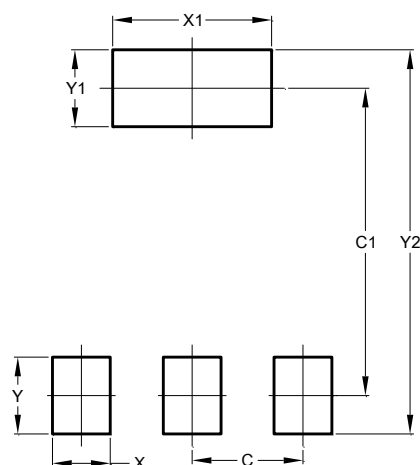


Package Outline Dimensions



SOT223			
Dim	Min	Max	Typ
A	1.55	1.65	1.60
A1	0.010	0.15	0.05
b	0.60	0.80	0.70
b1	2.90	3.10	3.00
C	0.20	0.30	0.25
D	6.45	6.55	6.50
E	3.45	3.55	3.50
E1	6.90	7.10	7.00
e	-	-	4.60
e1	-	-	2.30
L	0.85	1.05	0.95
Q	0.84	0.94	0.89
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
C	2.30
C1	6.40
X	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00

For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device Terminals and PCB tracking.